





N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _A = +25°C
50V	1.6Ω @ $V_{GS} = 10V$	500 mA
507	2.5Ω @ $V_{GS} = 4.5V$	200 mA

Features and Benefits

- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected to 2KV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Mechanical Data

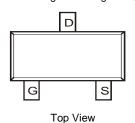
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (§3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

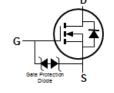




SOT23

Top View





Equivalent Circuit

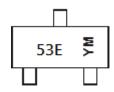
Ordering Information (Note 5)

Part Number	Case	Packaging
DMN53D0LQ-7	SOT23	3,000/Tape & Reel
DMN53D0LQ-13	SOT23	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



53E = Product Type Marking Code YM = Date Code Marking Y or = Year (ex: B = 2014) M = Month (ex: 9 = September)

Date Code Key

Year	2014	20	15	2016	2017	20	018	2019	2020	2	021	2022
Code	В	(C	D	Е		F	G	Н		1	J
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain Source Voltage	V _{DSS}	50	V
Gate-Source Voltage	V_{GSS}	±20	V
Drain Current (Note 7)	I _D	500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P_{D}	370	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ hetaJA}$	344	°C/W
Total Power Dissipation (Note 7)	P_{D}	540	mW
Thermal Resistance, Junction to Ambient (Note 7)	$R_{ hetaJA}$	236	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

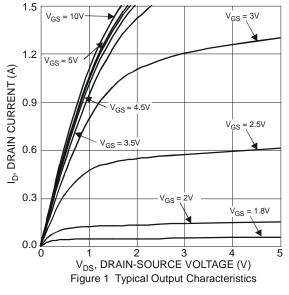
Electrical Character istics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

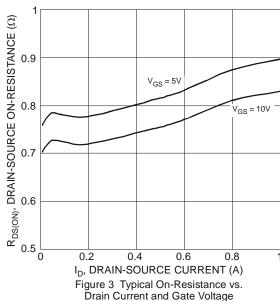
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)			· ·	1		1	
Drain-Source Breakdown Voltage	BV _{DSS}	50	_		V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 50V, V_{GS} = 0V$	
Gate-Body Leakage	I _{GSS}	_	_	10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(th)}	0.8	_	1.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
		_	_	1.6		$V_{GS} = 10V, I_D = 500mA$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	_	2.5	Ω	$V_{GS} = 4.5V, I_D = 200mA$	
		_	_	4.5		$V_{GS} = 2.5V, I_D = 100mA$	
Source-Drain Diode Forward Voltage	V_{SD}	_	_	1.4	V	$V_{GS} = 0V, I_{S} = 500mA$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	46	_	pF		
Output Capacitance	C _{oss}		5.3		pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}		4.0	_	pF	71 - 1.0101112	
Total Gate Charge	Qg	_	0.6	_	nC	45)/)/ 40)/	
Gate-Source Charge	Qgs	_	0.2	_	nC	$V_{GS} = 4.5V, V_{DS} = 10V,$	
Gate-Drain Charge	Q _{gd}	_	0.1	_	nC	$I_D = 250 \text{mA}$	
Turn-On Delay Time	t _{D(on)}	_	2.7	_	ns		
Turn-On Rise Time	t _r	_	2.5	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(off)}	_	19	_	ns	$R_G = 25\Omega$, $I_D = 200 \text{mA}$	
Turn-Off Fall Time	t _f	_	11	_	ns		

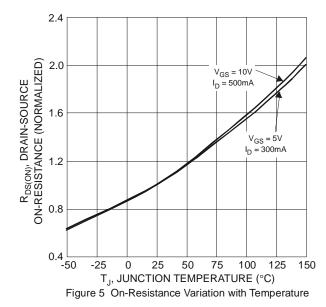
Notes:

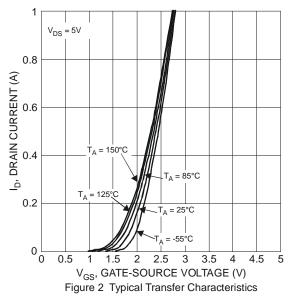
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.

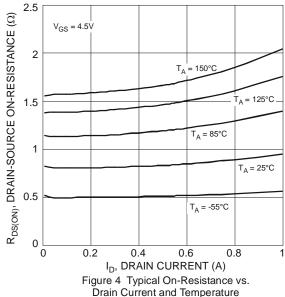












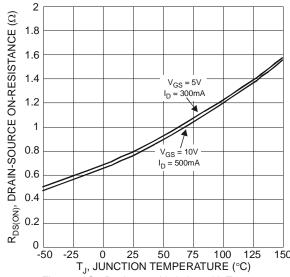


Figure 6 On-Resistance Variation with Temperature



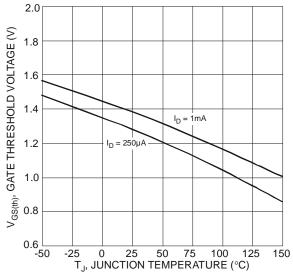
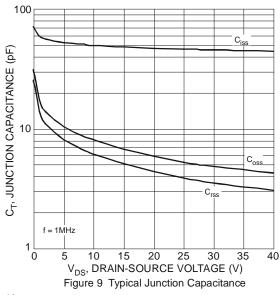
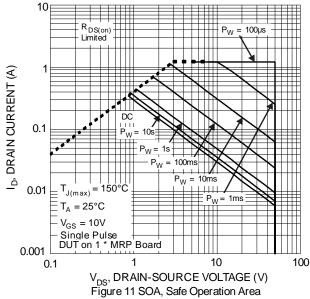
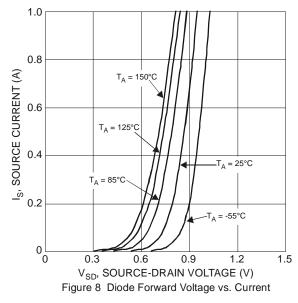
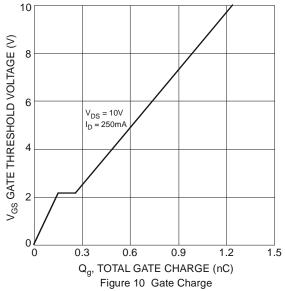


Figure 7 Gate Threshold Variation vs. Ambient Temperature

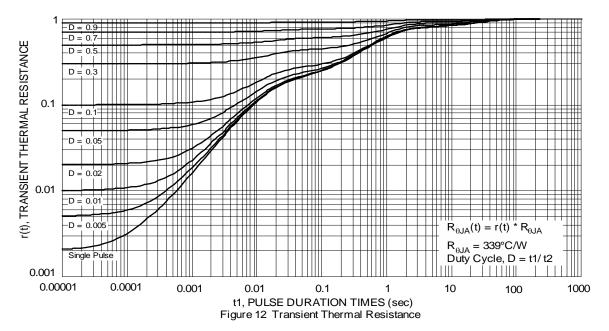








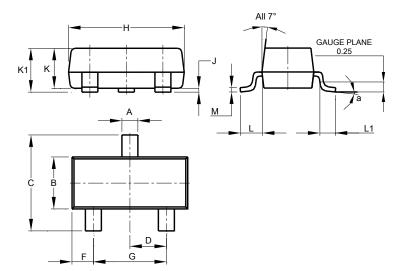






Package Outline Dimensions

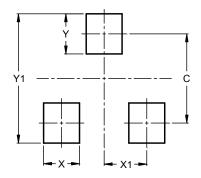
Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
M	0.085	0.150	0.110			
а	0°	8°				
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.0
X	0.8
X1	1.35
Υ	0.9
V1	2.0



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